



N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	7mΩ @ V _{GS} = 10V	14.1A
30V	10mΩ @ V _{GS} = 4.5V	11.8A
	15mΩ @ Vgs = 3.7V	9.6A

Features

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- · Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMT3006LFDFQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

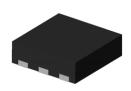
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Battery Management Application
- Power Management Functions
- DC-DC Converters

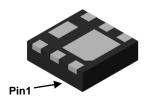
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)

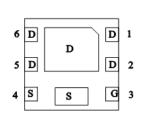
U-DFN2020-6 (Type F)



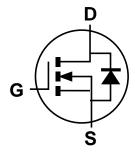
Top View



Bottom View



Pin Out Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Reel Size (inches)	Quantity per Reel
DMT3006LFDFQ-7	7	3,000
DMT3006LFDFQ-13	13	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1



6M = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	ı	J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



6M= Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	0	1	2	3	4	5	6	7	8
Code	U	ı		3	4	3	0		0

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			VDSS	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) Vgs = 10V	Steady State	T _A = +25°C T _A = +70°C	lo	14.1 12.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%))		I _{DM}	80	А
Continuous Source-Drain Diode Current (Note 6) T _A = +25°C			Is	2	Α
Avalanche Current (Note 7) L = 0.1mH	las	25	Α		
Avalanche Energy (Note 7) L = 0.1mH			Eas	31	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	155	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	60	°C/W
Thermal Resistance, Junction to Case (Note 6)	T _C = +25°C	Rejc	6.9	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)	-					
Drain-Source Breakdown Voltage	BVDSS	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current (T _J = +25°C)	IDSS	_	I	1	μΑ	V _{DS} = 24V, V _{GS} = 0V
Gate-Source Leakage	Igss		-	±100	nA	$V_{GS} = +20V, V_{DS} = 0V$ $V_{GS} = -16V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)		I .				, 50
Gate Threshold Voltage	V _{GS(TH)}	1.0	1.3	3.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			5.8	7		V _G S = 10V, I _D = 9A
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.8	10	mΩ	V _{GS} = 4.5V, I _D = 8A
			9.3	15		V _G S = 3.7V, I _D = 5A
Diode Forward Voltage	VsD	_	0.7	1.0	V	$V_{GS} = 0V$, $I_{S} = 2A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	1,155	_		V 45V V 6V
Output Capacitance	Coss	_	456	_	pF	$V_{DS} = 15V, V_{GS} = 0V,$ f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	72	_		1 = 1.000112
Gate Resistance	Rg	_	1.6		Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	16.7	_		
Total Gate Charge (V _{GS} = 10V)	Q _G	_	8.4	_	nC	\/ 45\/ I- 0A
Gate-Source Charge	Qgs	_	2.2	_	nc	$V_{DD} = 15V$, $I_D = 9A$
Gate-Drain Charge	Q_{GD}	_	3.5	_		
Turn-On Delay Time	td(on)	_	3.5	_		
Turn-On Rise Time	tR	_	5.5	_	no	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}	_	13.5	_	ns	$R_G = 3\Omega$, $I_D = 9A$
Turn-Off Fall Time	tF	_	4.6	_		
Reverse Recovery Time	trr	_	19.3		ns	L 1 5 \ di/dt 100 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Reverse Recovery Charge	Q _{RR}	_	8.6	_	nC	I _F = 1.5A, di/dt = 100A/μs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

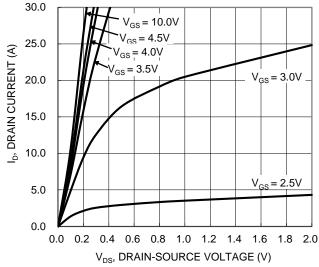
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

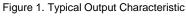
^{7.} Ias and Eas ratings are based on low frequency and duty cycles to keep T_J = +25°C.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.







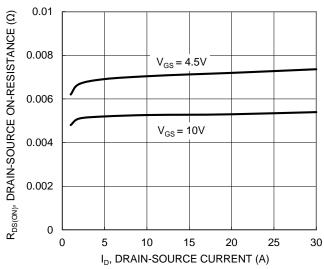


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

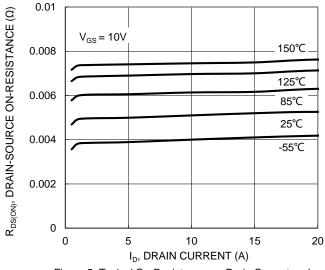


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

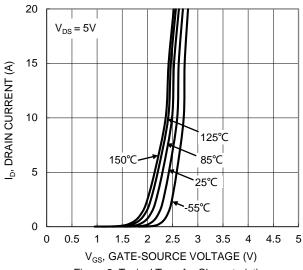


Figure 2. Typical Transfer Characteristic

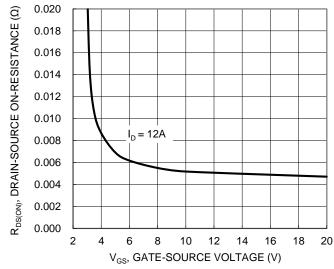


Figure 4. Typical Transfer Characteristic

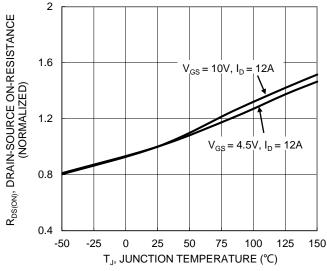


Figure 6. On-Resistance Variation with Temperature





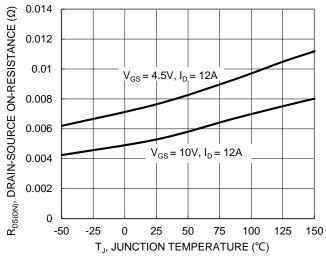


Figure 7. On-Resistance Variation with Temperature

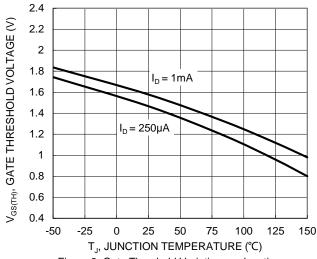
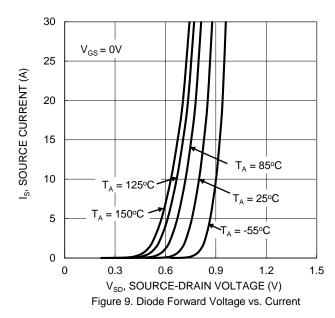
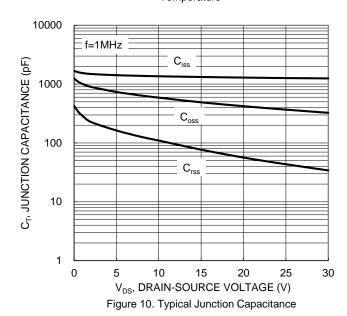


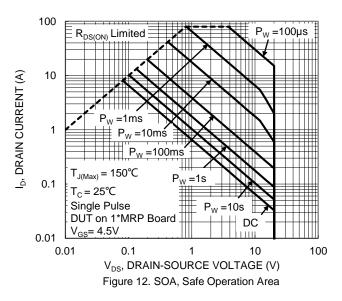
Figure 8. Gate Threshold Variation vs. Junction Temperature



8 6 $V_{GS}(V)$ 4 $V_{DS} = 15V, I_{D} = 12A$ 2 0 5 0 25

10 15 20 Q_{α} (nC) Figure 11. Gate Charge





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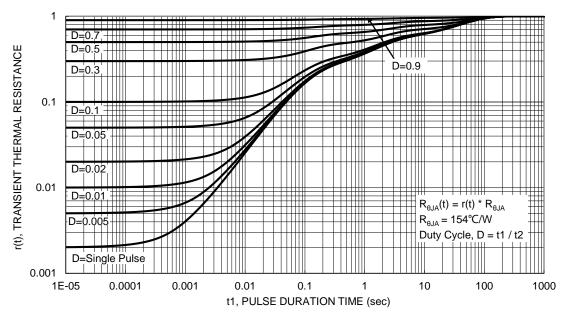


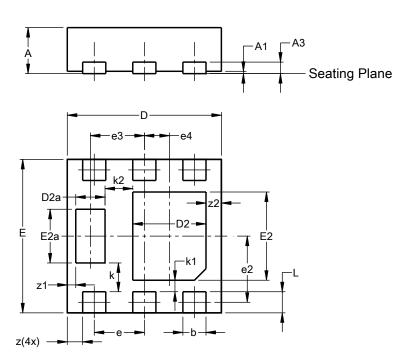
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

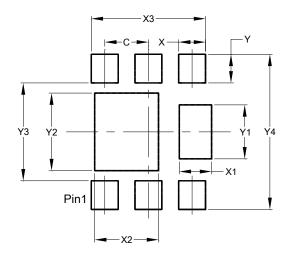


U-DFN2020-6						
		oe F)				
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A 1	0.00	0.05	0.03			
А3	-	-	0.15			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.85	1.05	0.95			
D2a	0.33	0.43	0.38			
Е	1.95	2.05	2.00			
E2	1.05	1.25	1.15			
E2a	0.65	0.75	0.70			
е	0.65 BSC					
e2	().863 BS	SC			
е3		0.70 BS	С			
e4	().325 BS	SC			
k		0.37 BS	С			
k1	0.15 BSC					
k2	0.36 BSC					
L	0.225	0.325	0.275			
Z	0.20 BSC					
z1	().110 BS	SC			
z2		0.20 BS	С			
All C	imens	ions in	mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)		
С	0.650		
X	0.400		
X1	0.480		
X2	0.950		
Х3	1.700		
Y	0.425		
Y1	0.800		
Y2	1.150		
Y3	1.450		
Y4	2.300		



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